



DIODE Type : 11ES1

FEATURES

- * Miniature Size
- * Low Forward Voltage drop
- * Low Reverse Leakage Current
- * High Surge Capability
- * 26mm and 52mm Inside Tape Spacing Package Available

OUTLINE DRAWING



Maximum Ratings

Approx Net Weight:0.17g

Rating	Symbol	11ES1			Unit
Repetitive Peak Reverse Voltage	V _{RRM}	100			V
Non-repetitive Peak Reverse Voltage	V _{RSM}	250			V
Average Rectified Output Current	I _O	0.98	Ta=25℃ *1	50Hz Half Sine Wave Resistive Load	A
		1.0	Ta=50℃ *2		
RMS Forward Current	I _{F(RMS)}	1.57			A
Surge Forward Current	I _{FSM}	45	50Hz Half Sine Wave,1cycle, Non-repetitive		A
Operating JunctionTemperature Range	T _{jw}	- 40 to + 150			℃
Storage Temperature Range	T _{stg}	- 40 to + 150			℃

Electrical • Thermal Characteristics

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Reverse Current	I_{RM}	$T_j = 25^{\circ}\text{C}$, $V_{RM} = V_{RRM}$	-	-	50	μA
Peak Forward Voltage	V_{FM}	$T_j = 25^{\circ}\text{C}$, $I_{FM} = 1.0\text{A}$	-	-	1.0	V
Thermal Resistance	$R_{th(j-a)}$	Junction to Ambient	*1	-	140	$^{\circ}\text{C/W}$
			*2	-	110	

*1:Without Fin or P.C. Board

*2:P.C. Board Mounted (L=3mm,Print Land=5x5mm,Both Sides)

11ES1 OUTLINE DRAWING (Dimensions in mm)

